

# ON Semiconductor

## Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

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# 2N5088, 2N5089

## Amplifier Transistors

### NPN Silicon

#### Features

- Pb-Free Packages are Available\*

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage 2N5088 2N5089	$V_{CEO}$	30 25	Vdc
Collector – Base Voltage 2N5088 2N5089	$V_{CB0}$	35 30	Vdc
Emitter – Base Voltage	$V_{EBO}$	3.0	Vdc
Collector Current – Continuous	$I_C$	50	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

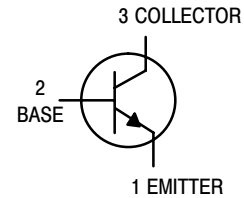
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1.  $R_{\theta JA}$  is measured with the device soldered into a typical printed circuit board.

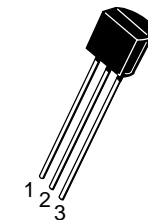


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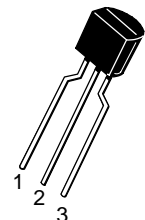
<http://onsemi.com>



TO-92  
CASE 29  
STYLE 1

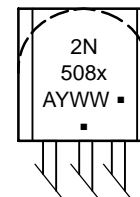


STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

#### MARKING DIAGRAM



x = 8 or 9

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
2N5088G	TO-92 (Pb-Free)	5000 Units/Bulk
2N2088RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel
2N5089G	TO-92 (Pb-Free)	5000 Units/Bulk
2N2089RLRE	TO-92	2000/Tape & Reel

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## 2N5088, 2N5089

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage (Note 2) ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	2N5088 2N5089	$V_{(BR)CEO}$	30 25	– –	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100\text{ }\mu\text{Adc}$ , $I_E = 0$ )	2N5088 2N5089	$V_{(BR)CBO}$	35 30	– –	Vdc
Collector Cutoff Current ( $V_{CB} = 20\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 15\text{ Vdc}$ , $I_E = 0$ )	2N5088 2N5089	$I_{CBO}$	– –	50 50	nAdc
Emitter Cutoff Current ( $V_{EB(off)} = 3.0\text{ Vdc}$ , $I_C = 0$ ) ( $V_{EB(off)} = 4.5\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	– –	50 100	nAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	2N5088 2N5089	$h_{FE}$	300 400	900 1200	–
( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	2N5088 2N5089		350 450	– –	
( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) (Note 2)	2N5088 2N5089		300 400	– –	
Collector – Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ )		$V_{CE(sat)}$	–	0.5	Vdc
Base – Emitter On Voltage ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) (Note 2)		$V_{BE(on)}$	–	0.8	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>					
Current – Gain – Bandwidth Product ( $I_C = 500\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 20\text{ MHz}$ )		$f_T$	50	–	MHz
Collector – Base Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )		$C_{cb}$	–	4.0	pF
Emitter – Base Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )		$C_{eb}$	–	10	pF
Small – Signal Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	2N5088 2N5089	$h_{fe}$	350 450	1400 1800	–
Noise Figure ( $I_C = 100\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	2N5088 2N5089	NF	– –	3.0 2.0	dB

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

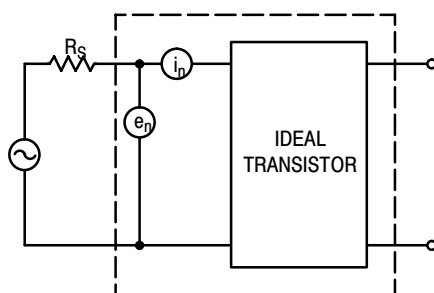


Figure 1. Transistor Noise Model

# 2N5088, 2N5089

## NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

### NOISE VOLTAGE

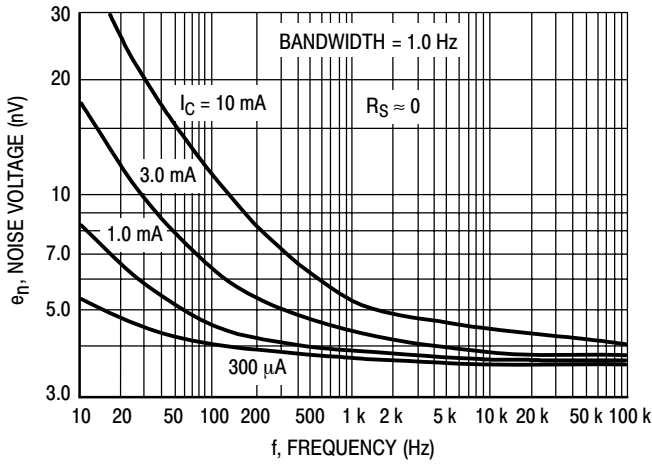


Figure 2. Effects of Frequency

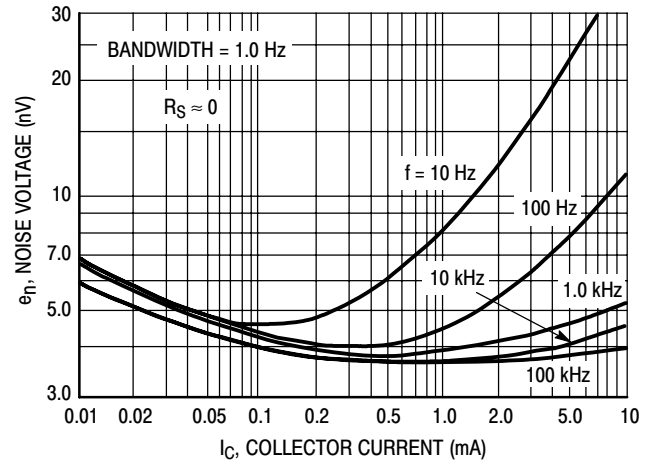


Figure 3. Effects of Collector Current

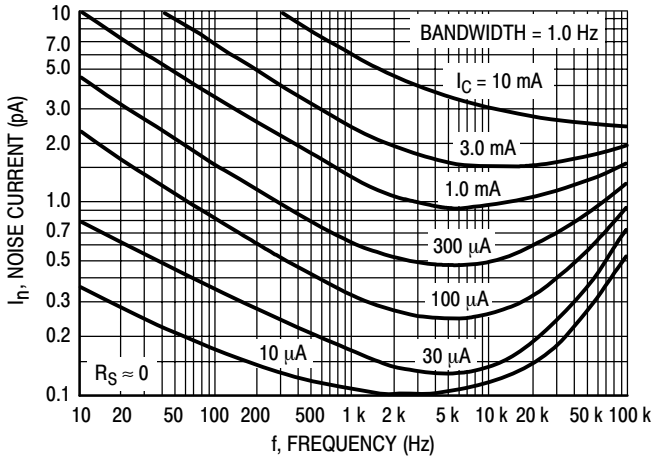


Figure 4. Noise Current

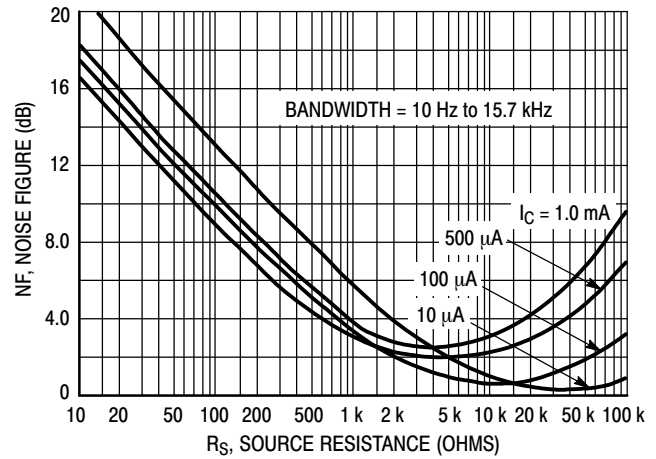


Figure 5. Wideband Noise Figure

### 100 Hz NOISE DATA

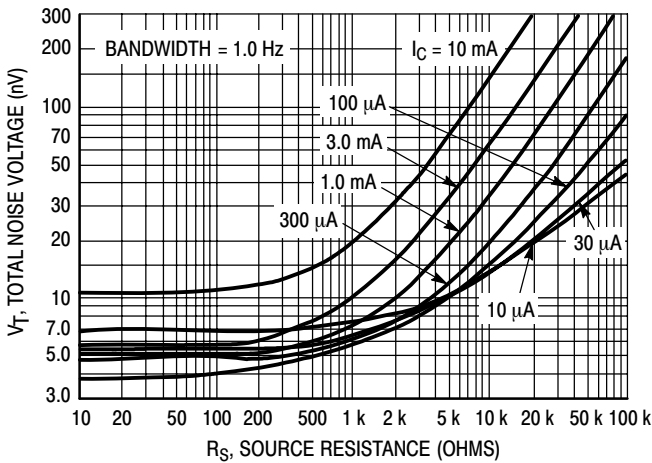


Figure 6. Total Noise Voltage

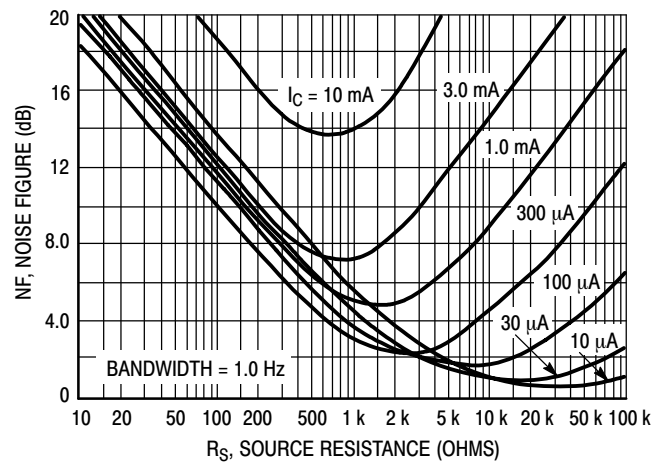


Figure 7. Noise Figure

2N5088, 2N5089

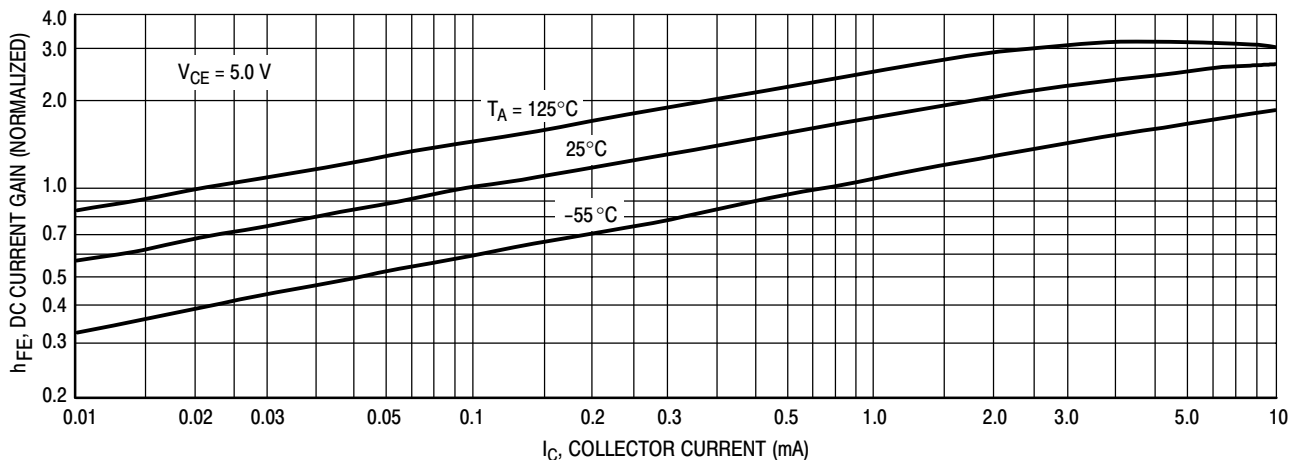


Figure 8. DC Current Gain

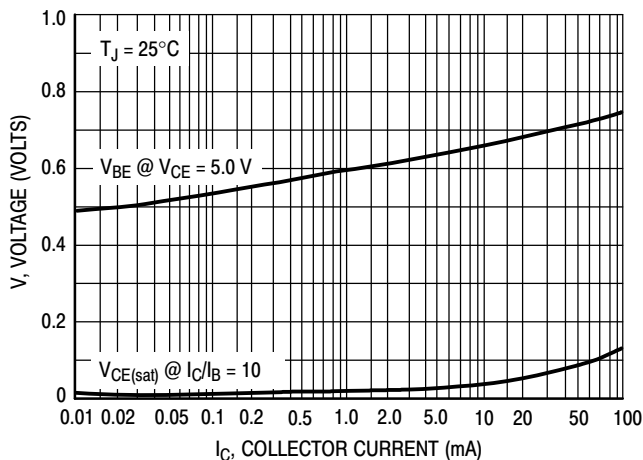


Figure 9. "On" Voltages

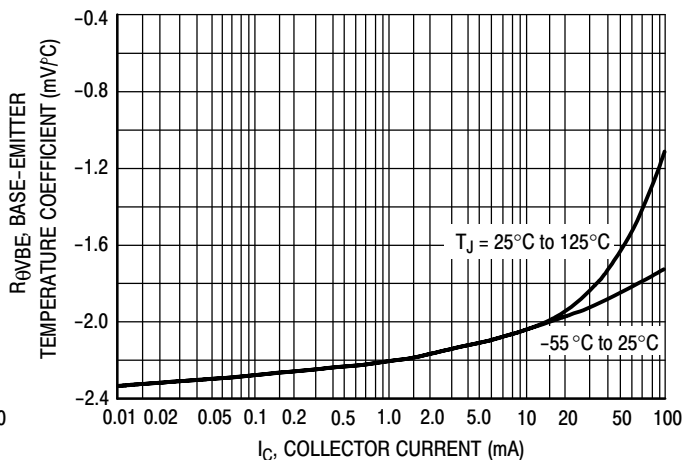


Figure 10. Temperature Coefficients

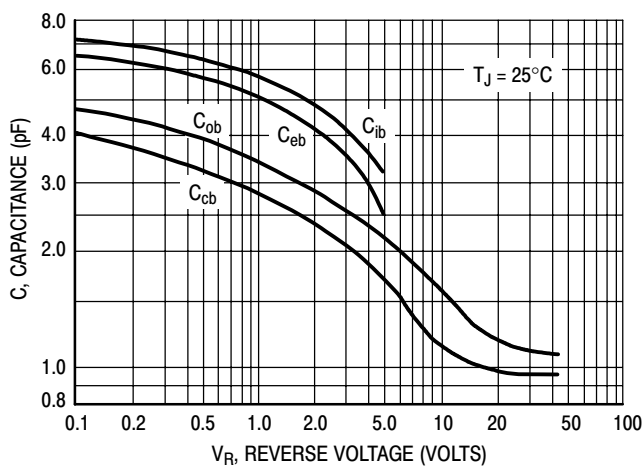


Figure 11. Capacitance

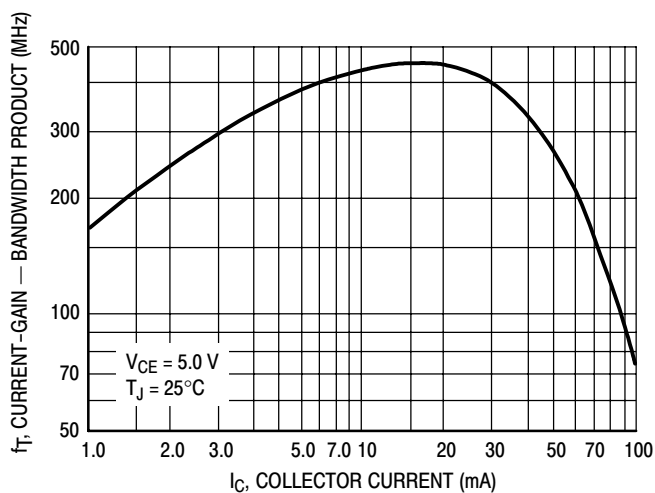


Figure 12. Current-Gain — Bandwidth Product

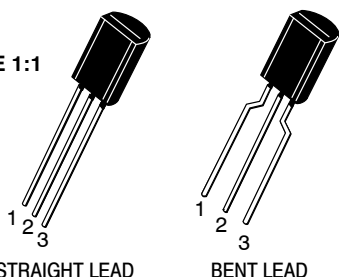
# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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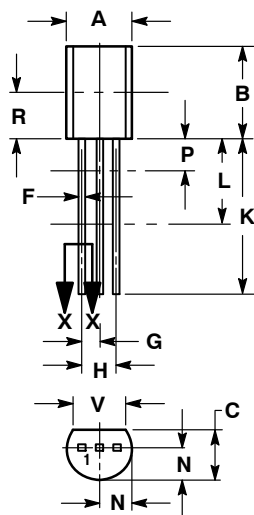


SCALE 1:1

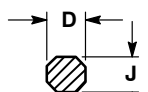


### TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE A

DATE 08 MAY 2012



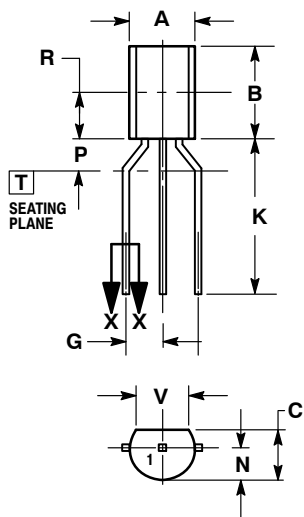
STRAIGHT LEAD



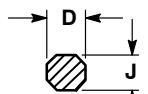
SECTION X-X

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



BENT LEAD



SECTION X-X

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

### STYLES ON PAGE 2

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**TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE A**

DATE 08 MAY 2012

- |   |  |  |   |   |
|---|--|--|---|---|
| <p>STYLE 1:<br/>PIN 1. EMITTER<br/>2. BASE<br/>3. COLLECTOR</p>             | <p>STYLE 2:<br/>PIN 1. BASE<br/>2. EMITTER<br/>3. COLLECTOR</p>                | <p>STYLE 3:<br/>PIN 1. ANODE<br/>2. ANODE<br/>3. CATHODE</p>               | <p>STYLE 4:<br/>PIN 1. CATHODE<br/>2. CATHODE<br/>3. ANODE</p>            | <p>STYLE 5:<br/>PIN 1. DRAIN<br/>2. SOURCE<br/>3. GATE</p>            |
| <p>STYLE 6:<br/>PIN 1. GATE<br/>2. SOURCE &amp; SUBSTRATE<br/>3. DRAIN</p>  | <p>STYLE 7:<br/>PIN 1. SOURCE<br/>2. DRAIN<br/>3. GATE</p>                     | <p>STYLE 8:<br/>PIN 1. DRAIN<br/>2. GATE<br/>3. SOURCE &amp; SUBSTRATE</p> | <p>STYLE 9:<br/>PIN 1. BASE 1<br/>2. EMITTER<br/>3. BASE 2</p>            | <p>STYLE 10:<br/>PIN 1. CATHODE<br/>2. GATE<br/>3. ANODE</p>          |
| <p>STYLE 11:<br/>PIN 1. ANODE<br/>2. CATHODE &amp; ANODE<br/>3. CATHODE</p> | <p>STYLE 12:<br/>PIN 1. MAIN TERMINAL 1<br/>2. GATE<br/>3. MAIN TERMINAL 2</p> | <p>STYLE 13:<br/>PIN 1. ANODE 1<br/>2. GATE<br/>3. CATHODE 2</p>           | <p>STYLE 14:<br/>PIN 1. EMITTER<br/>2. COLLECTOR<br/>3. BASE</p>          | <p>STYLE 15:<br/>PIN 1. ANODE 1<br/>2. CATHODE<br/>3. ANODE 2</p>     |
| <p>STYLE 16:<br/>PIN 1. ANODE<br/>2. GATE<br/>3. CATHODE</p>                | <p>STYLE 17:<br/>PIN 1. COLLECTOR<br/>2. BASE<br/>3. EMITTER</p>               | <p>STYLE 18:<br/>PIN 1. ANODE<br/>2. CATHODE<br/>3. NOT CONNECTED</p>      | <p>STYLE 19:<br/>PIN 1. GATE<br/>2. ANODE<br/>3. CATHODE</p>              | <p>STYLE 20:<br/>PIN 1. NOT CONNECTED<br/>2. CATHODE<br/>3. ANODE</p> |
| <p>STYLE 21:<br/>PIN 1. COLLECTOR<br/>2. EMITTER<br/>3. BASE</p>            | <p>STYLE 22:<br/>PIN 1. SOURCE<br/>2. GATE<br/>3. DRAIN</p>                    | <p>STYLE 23:<br/>PIN 1. GATE<br/>2. SOURCE<br/>3. DRAIN</p>                | <p>STYLE 24:<br/>PIN 1. EMITTER<br/>2. COLLECTOR/ANODE<br/>3. CATHODE</p> | <p>STYLE 25:<br/>PIN 1. MT 1<br/>2. GATE<br/>3. MT 2</p>              |
| <p>STYLE 26:<br/>PIN 1. V<sub>CC</sub><br/>2. GROUND 2<br/>3. OUTPUT</p>    | <p>STYLE 27:<br/>PIN 1. MT<br/>2. SUBSTRATE<br/>3. MT</p>                      | <p>STYLE 28:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. GATE</p>               | <p>STYLE 29:<br/>PIN 1. NOT CONNECTED<br/>2. ANODE<br/>3. CATHODE</p>     | <p>STYLE 30:<br/>PIN 1. DRAIN<br/>2. GATE<br/>3. SOURCE</p>           |
| <p>STYLE 31:<br/>PIN 1. GATE<br/>2. DRAIN<br/>3. SOURCE</p>                 | <p>STYLE 32:<br/>PIN 1. BASE<br/>2. COLLECTOR<br/>3. EMITTER</p>               | <p>STYLE 33:<br/>PIN 1. RETURN<br/>2. INPUT<br/>3. OUTPUT</p>              | <p>STYLE 34:<br/>PIN 1. INPUT<br/>2. GROUND<br/>3. LOGIC</p>              | <p>STYLE 35:<br/>PIN 1. GATE<br/>2. COLLECTOR<br/>3. EMITTER</p>      |

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